Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology

3. Applications

- Low power DC-to-DC converters
- Load switching
- Battery management
- Battery powered portable equipment

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-	-4.3	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C		-	58	74	mΩ



20 V, single P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D
2	S	source		
3	D	drain	1	G S 017aaa257

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV65XP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65XP	%M9

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-4.3	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.8	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	480	mW
			[1]	-	833	mW
		T _{sp} = 25 °C		-	4165	mW

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20 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{sp} = 25 °C		-	-1.6	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm². Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

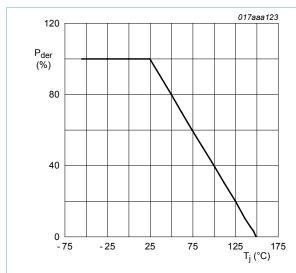


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

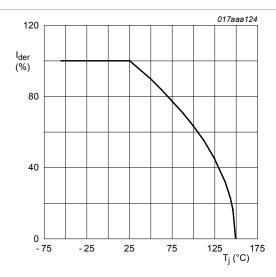


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

20 V, single P-channel Trench MOSFET

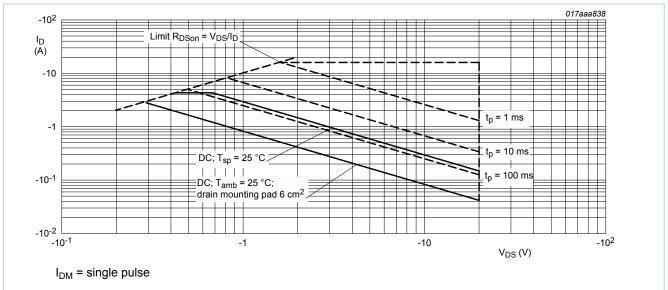


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

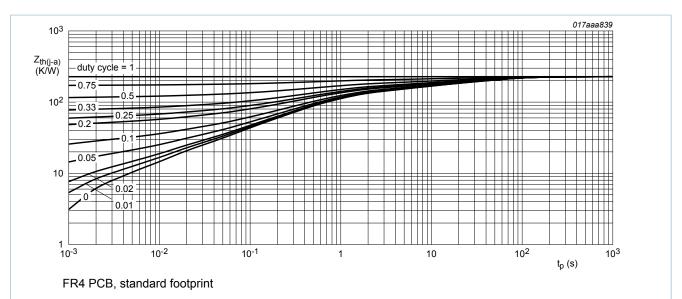
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance from junction to ambient	-	[1]	-	230	260	K/W
			[2]	-	125	150	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	25	30	K/W

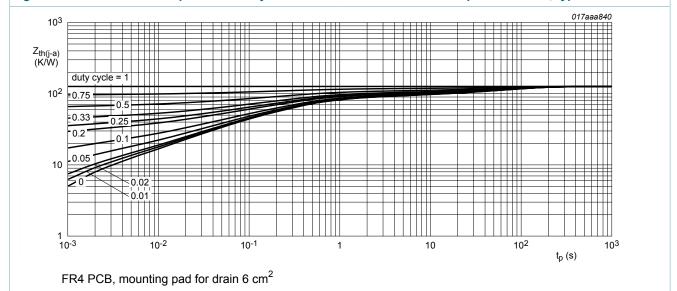
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

4/14

20 V, single P-channel Trench MOSFET



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C		-0.47	-0.65	-0.9	V	
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	μA	
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C		-	-	-100	μΑ	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	58	74	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.8 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	82	105	mΩ
		V_{GS} = -2.5 V; I_D = -2.3 A; T_j = 25 °C	-	67	92	mΩ
		V_{GS} = -1.8 V; I_D = -1 A; T_j = 25 °C	-	87	135	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I_{D} = -2.8 A; T_{j} = 25 °C	-	15	-	S
Dynamic cl	haracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = -6 V; I_{D} = -2.8 A; V_{GS} = -4.5 V; T_{j} = 25 °C	-	7.7	-	nC
Q _{GS}	gate-source charge		-	1	-	nC
Q_{GD}	gate-drain charge		-	1.65	-	nC
C _{iss}	input capacitance	V _{DS} = -20 V; f = 1 MHz; V _{GS} = 0 V;	-	744	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	65	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -6 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	7	-	ns
t _r	rise time	T _j = 25 °C; I _D = -1 A	-	18	-	ns
t _{d(off)}	turn-off delay time		-	135	-	ns
t _f	fall time		-	68	-	ns
Source-dra	nin diode		1		1	
V _{SD}	source-drain voltage	$I_S = -0.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V

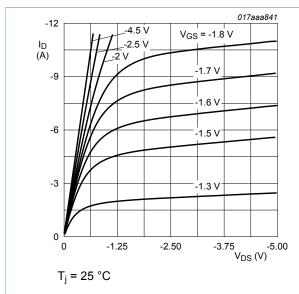


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

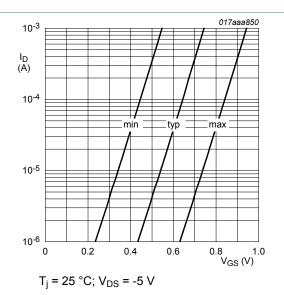


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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20 V, single P-channel Trench MOSFET

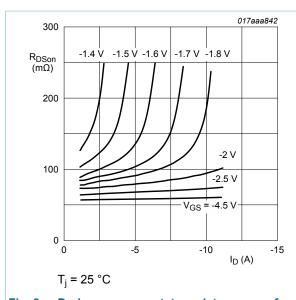


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

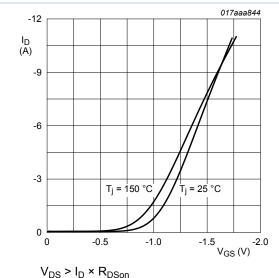


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

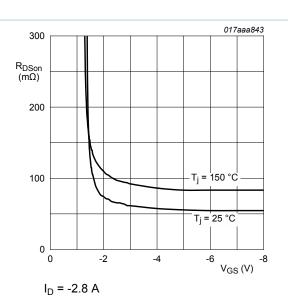


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

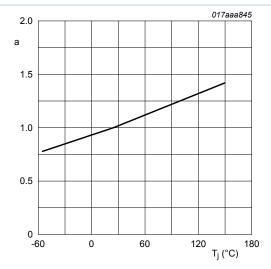


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

20 V, single P-channel Trench MOSFET

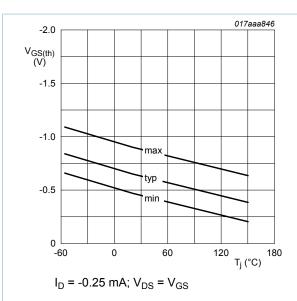


Fig. 12. Gate-source threshold voltage as a function of junction temperature

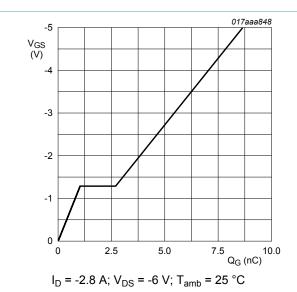
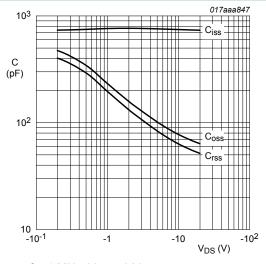


Fig. 14. Gate-source voltage as a function of gate charge; typical values



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

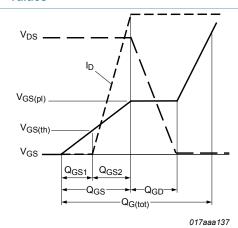
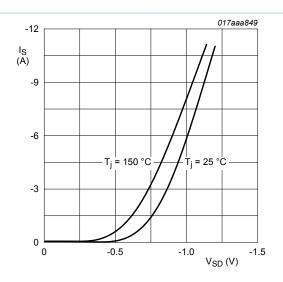


Fig. 15. Gate charge waveform definitions

20 V, single P-channel Trench MOSFET



 $V_{GS} = 0 V$

(1) $T_j = 150 \,^{\circ}\text{C}$

(2) $T_i = 25 \,^{\circ}\text{C}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

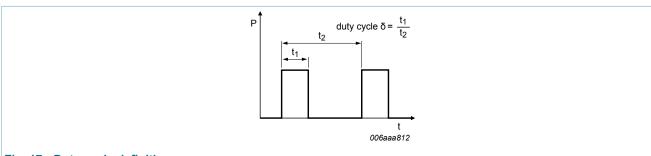
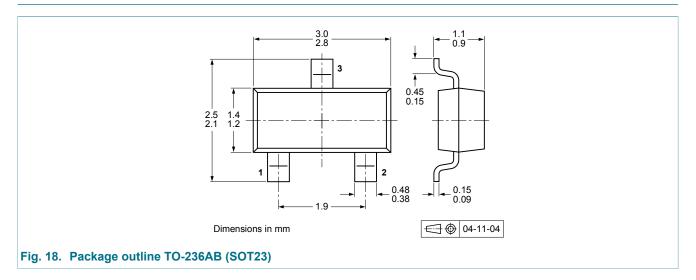


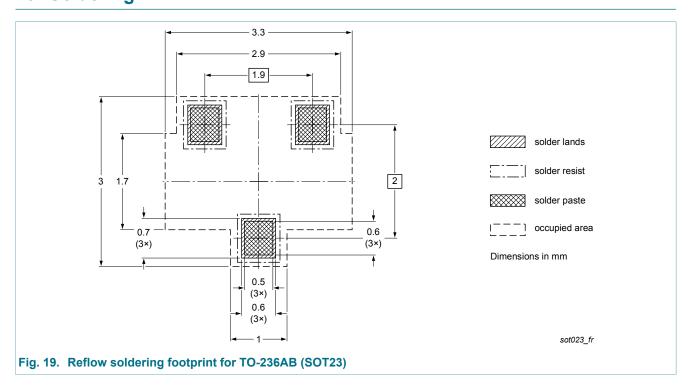
Fig. 17. Duty cycle definition

20 V, single P-channel Trench MOSFET

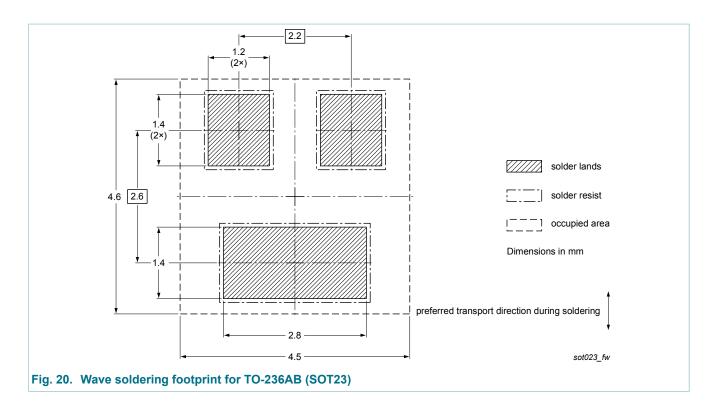
12. Package outline



13. Soldering



20 V, single P-channel Trench MOSFET



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMV65XP v.2	20130212	Product data sheet	-	PMV65XP v.1			
Modifications:	Pinning inform	Pinning information corrected					
PMV65XP v.1	20120921	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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20 V, single P-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	9
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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